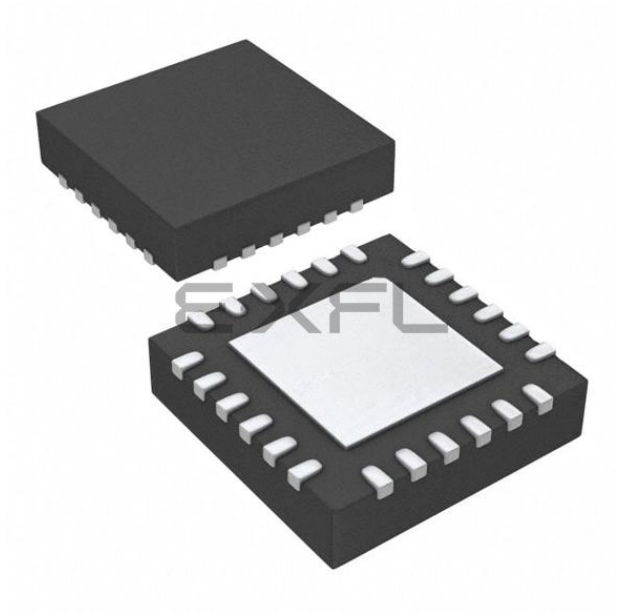

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	17
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg110f64g-a-qfn24

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 8), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8) , unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1]Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			25	MHz
f_{AHB}	Internal AHB clock frequency			25	MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		1.6	3.50	µA
I_{EM3}	EM3 current	EM3 current (ULFRCO enabled, LFRCO/LFXO disabled), V_{DD}= 3.0 V, T_{AMB}=25°C		0.6	0.90	µA
		EM3 current (ULFRCO enabled, LFRCO/LFXO disabled), V_{DD}= 3.0 V, T_{AMB}=85°C		1.2	2.65	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.035	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.18	0.480	µA

3.4.1 EM0 Current Consumption

Figure 3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 24 MHz

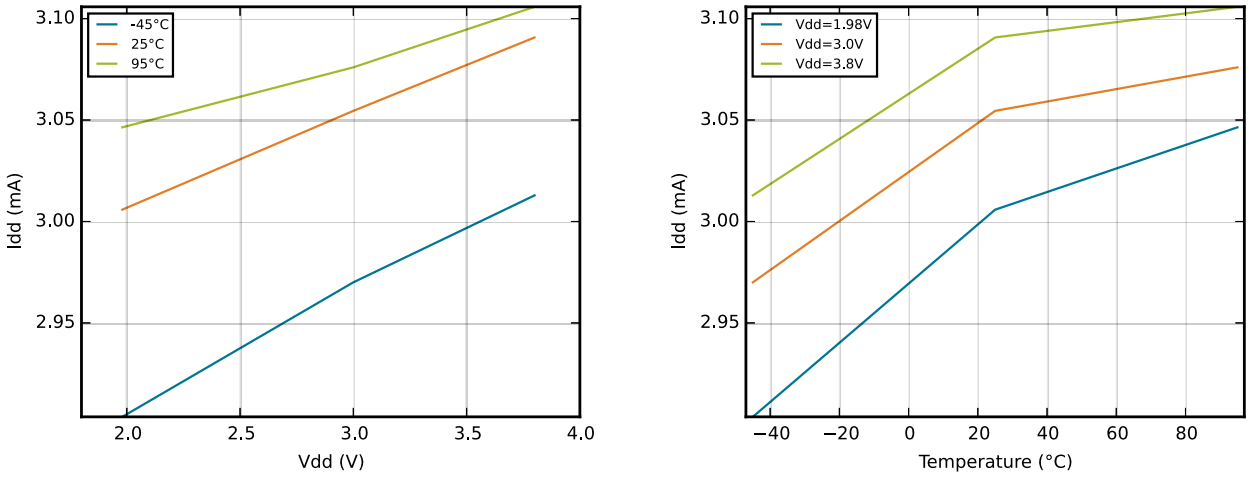


Figure 3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21 MHz

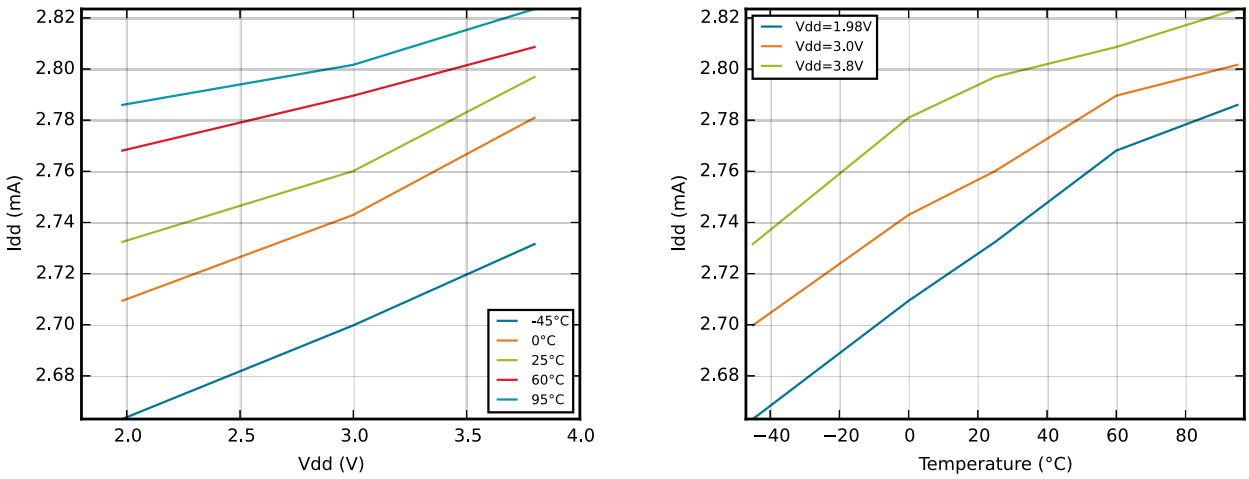


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz

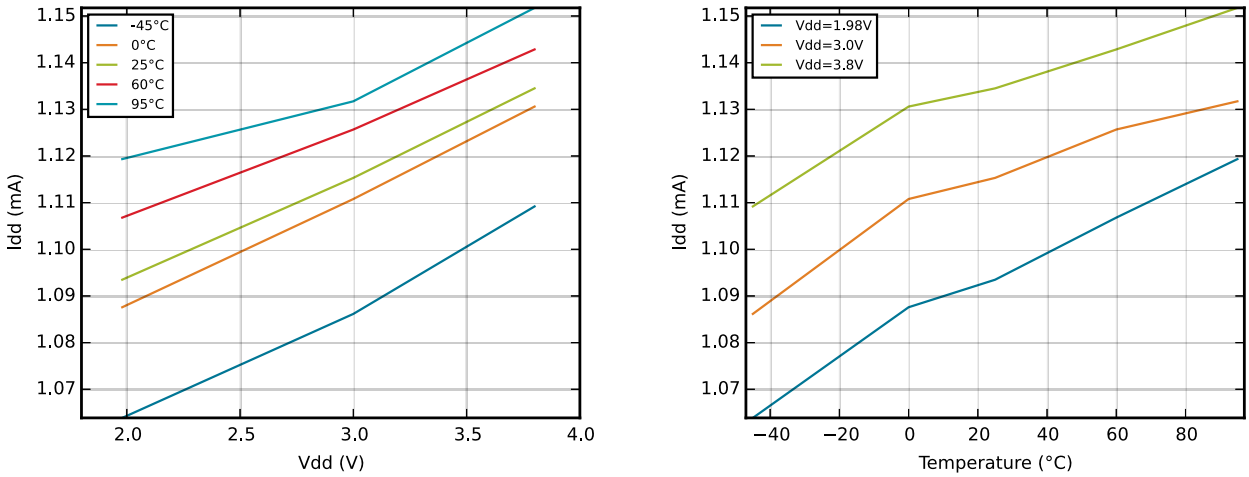
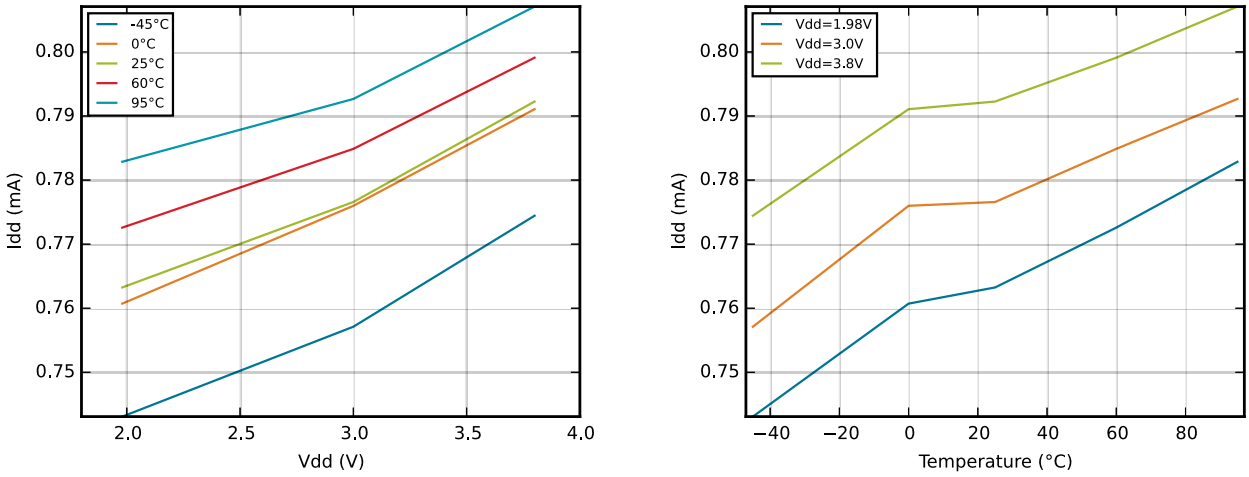
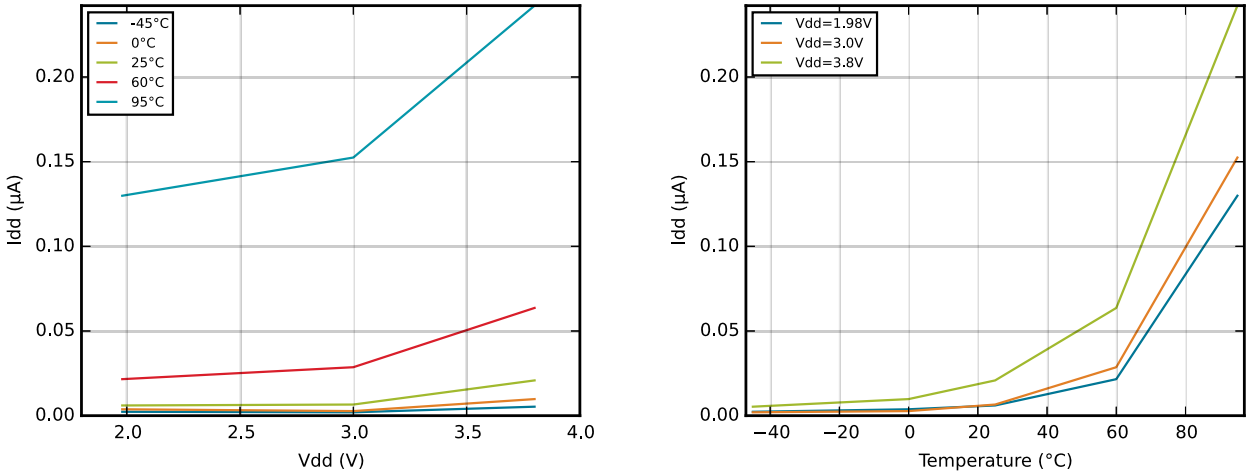


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz



3.4.5 EM4 Current Consumption

Figure 3.13. EM4 current consumption.



3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Typ	Max	Unit
t_{EM10}	Transition time from EM1 to EM0		0		HF-CORE-CLK cycles
t_{EM20}	Transition time from EM2 to EM0		2		µs
t_{EM30}	Transition time from EM3 to EM0		2		µs
t_{EM40}	Transition time from EM4 to EM0		163		µs

3.6 Power Management

The EFM32HG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.71	1.86	1.98	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85		V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{P_ERASE}	Page erase time		20	20.4	20.8	ms
t_{D_ERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1]Measured at 25°C

3.8 General Purpose Input Output

Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V_{DD}		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V_{DD}		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V_{DD}			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V_{DD}			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V_{DD}			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V_{DD}			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V_{DD}		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V_{DD}		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V_{DD}	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V_{DD}	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V_{DD}	V
		Sinking 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V_{DD}	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or Vdd		±0.1	±40	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed		10		50	ns

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	by the glitch suppression filter					
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance C_L=12.5-25pF.	20+0.1C_L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C_L=350-600pF	20+0.1C_L		250	ns
V_{IOHYST}	I/O pin hysteresis (V_{IOTHR+} - V_{IOTHR-})	V_{DD} = 1.98 - 3.8 V	0.1V_{DD}			V

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		5		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		1100		ms

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported frequency, any mode		4		25	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 25 MHz		30	100	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		785		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		70		dB
$SINAD_{ADC}$	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB

Figure 3.26. Integral Non-Linearity (INL)

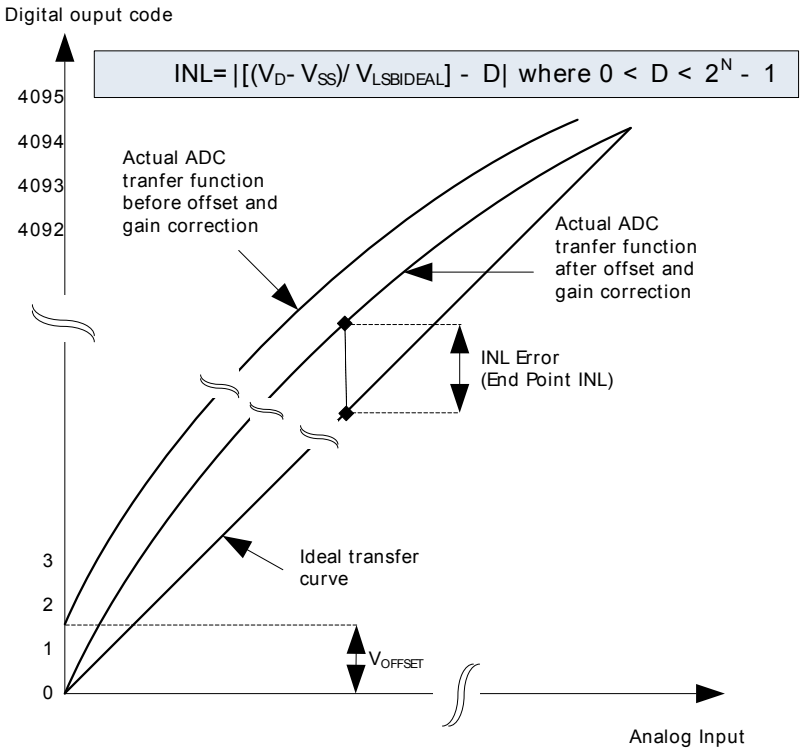


Figure 3.27. Differential Non-Linearity (DNL)

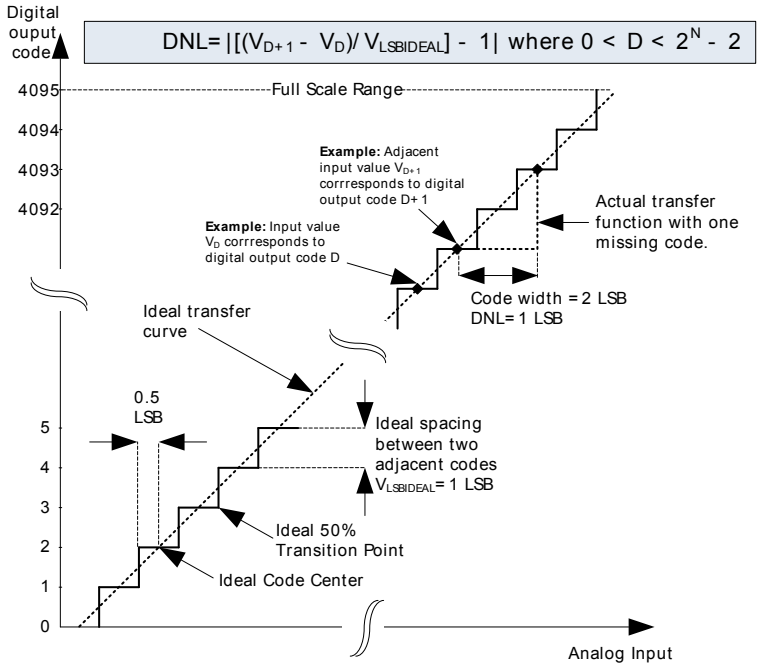
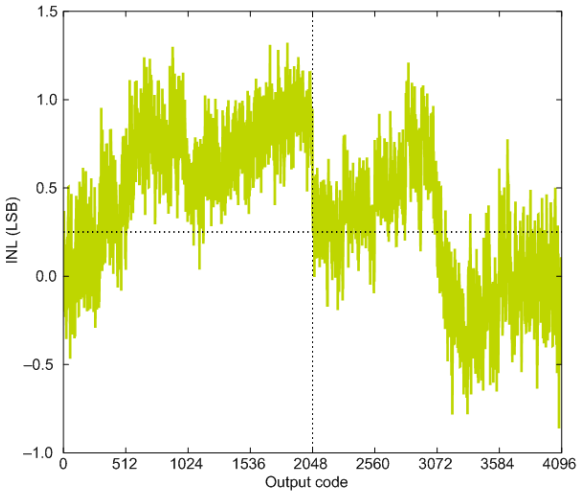
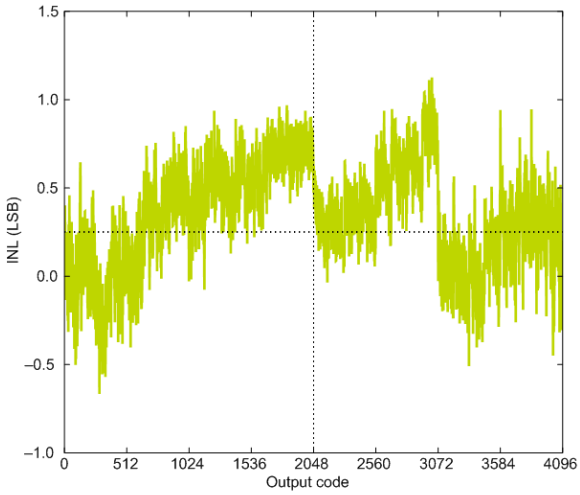


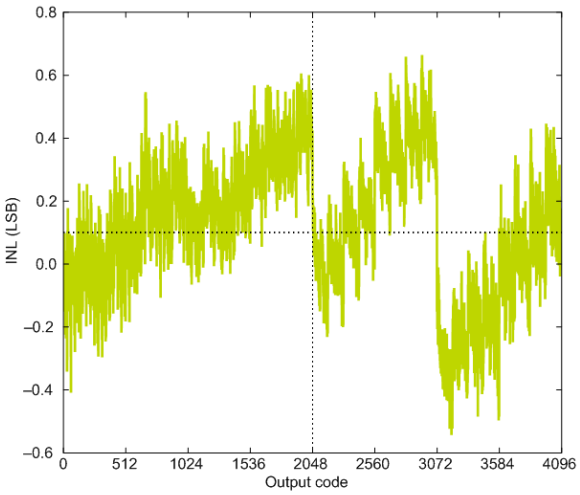
Figure 3.29. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



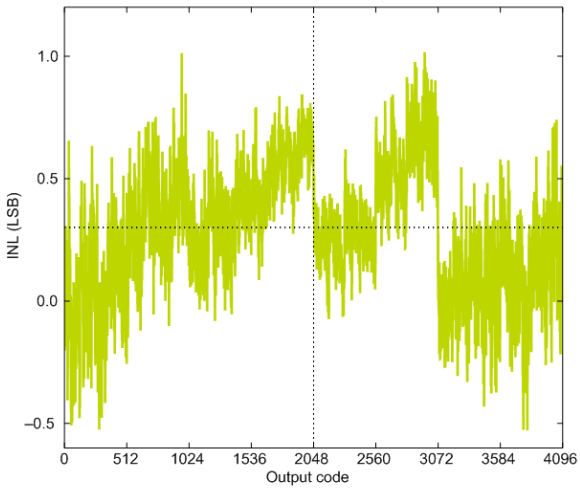
1.25V Reference



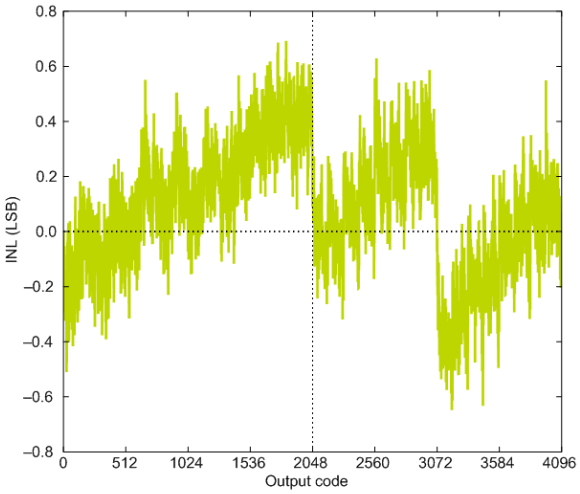
2.5V Reference



2XVDDVSS Reference

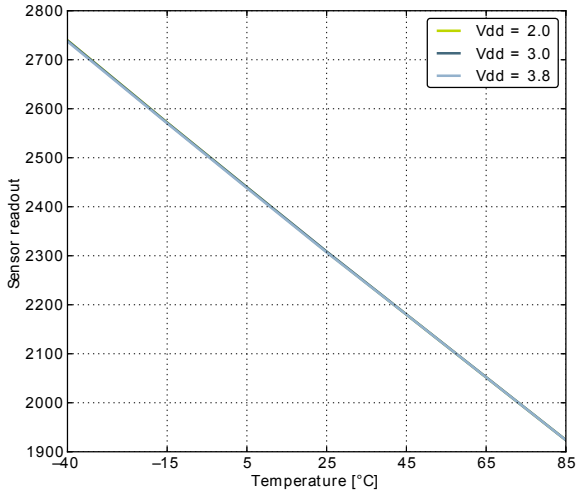


5VDIFF Reference



VDD Reference

Figure 3.33. ADC Temperature sensor readout



3.11 Current Digital Analog Converter (IDAC)

Table 3.16. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.0		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.79		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0V, STEPSEL=0x10		0.3		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		11.7		nA/V

Table 3.17. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		15.1		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.30		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.2		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		12.5		nA/V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			8.5		µA
I_{STEP}	Step size			0.5		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.62		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		94.4		nA/V

Table 3.22. IDAC Range 3 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		18.7		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			33.9		µA
I_{STEP}	Step size			2.0		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100 mV		3.54		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		159.5		nA/V

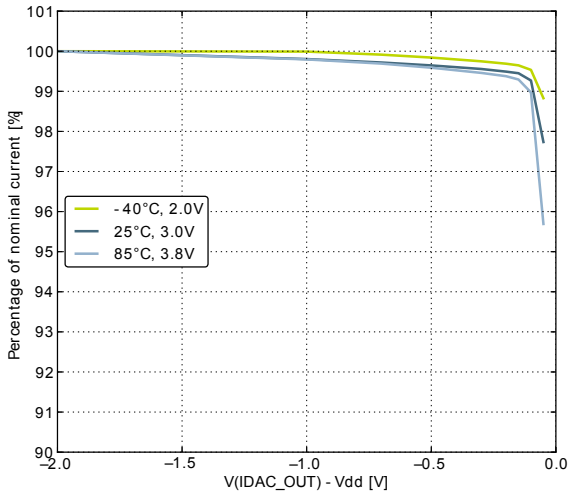
Table 3.23. IDAC Range 3 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		62.5		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			34.1		µA
I_{STEP}	Step size			2.0		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		1.75		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		148.6		nA/V

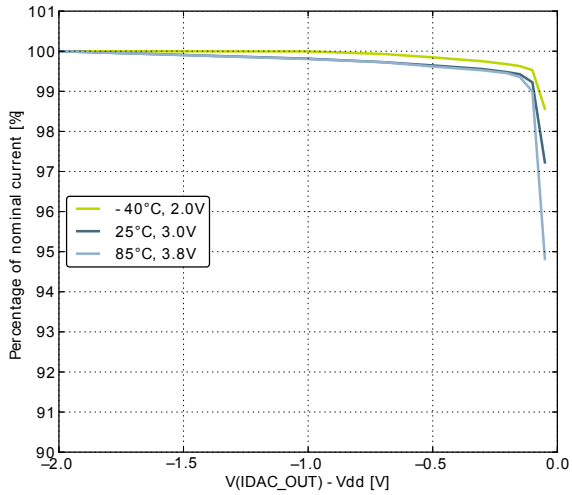
Table 3.24. IDAC

Symbol	Parameter	Min	Typ	Max	Unit
$t_{IDACSTART}$	Start-up time, from enabled to output settled		40		µs

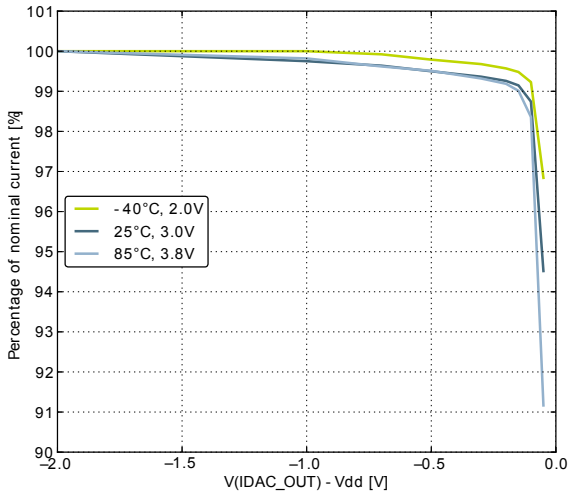
Figure 3.34. IDAC Source Current as a function of voltage on IDAC_OUT



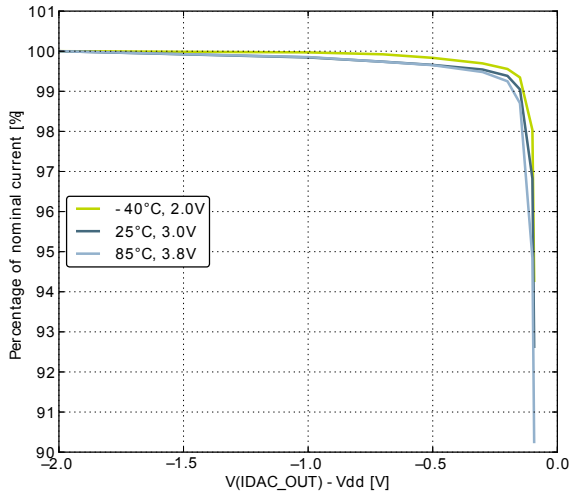
Range 0



Range 1



Range 2



Range 3

Table 3.28. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and START condition	1.3			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32HG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 5).

Table 3.29. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and START condition	0.5			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32HG Reference Manual.

3.15 Digital Peripherals

Table 3.30. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		7.5		µA/MHz
I_{I2C}	I2C current	I2C idle current, clock enabled		6.25		µA/MHz
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		8.75		µA/MHz
I_{PCNT}	PCNT current	PCNT idle current, clock enabled		100		nA
I_{RTC}	RTC current	RTC idle current, clock enabled		100		nA
I_{AES}	AES current	AES idle current, clock enabled		2.5		µA/MHz

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
PCNT0_S1IN	PC14		PC1	PD7	PB11			Pulse Counter PCNT0 input number 1.
PRS_CH0	PA0		PC14	PF2				Peripheral Reflex System PRS, channel 0.
PRS_CH1			PC15	PE12				Peripheral Reflex System PRS, channel 1.
PRS_CH2	PC0			PE13				Peripheral Reflex System PRS, channel 2.
PRS_CH3	PC1			PA0				Peripheral Reflex System PRS, channel 3.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1					PC0	PF1	PA0	Timer 0 Capture Compare input / output channel 1.
TIM0_CC2					PC1	PF2	PF2	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI1		PC14					PC14	Timer 0 Complimentary Deat Time Insertion channel 1.
TIM0_CDTI2		PC15					PC15	Timer 0 Complimentary Deat Time Insertion channel 2.
TIM1_CC0				PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14			PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11				Timer 1 Capture Compare input / output channel 2.
TIM2_CC0				PF2				Timer 2 Capture Compare input / output channel 0.
TIM2_CC1				PE12				Timer 2 Capture Compare input / output channel 1.
TIM2_CC2				PE13				Timer 2 Capture Compare input / output channel 2.
US0_CLK	PE12			PC15	PB13	PB13	PE12	USART0 clock input / output.
US0_CS	PE13			PC14	PB14	PB14	PE13	USART0 chip select input / output.
US0_RX				PE12	PB8	PC1	PC1	USART0 Asynchronous Receive. USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX				PE13	PB7	PC0	PC0	USART0 Asynchronous Transmit.Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0	PC15	PB11			USART1 clock input / output.
US1_CS	PB8		PF1	PC14	PC14	PC0		USART1 chip select input / output.
US1_RX	PC1		PD6	PD6	PA0			USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0		PD7	PD7	PF2	PC1		USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32HG110* is shown in Table 4.3 (p. 56) . Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.4. QFN24 (Dimensions in mm)

Symbol	A	A1	A3	b	D	E	D2	E2	e	L	L1	aaa	bbb	ccc	ddd	eee
Min	0.80	0.00	0.203 REF	0.25	5.00 BSC	5.00 BSC	3.50	3.50	0.65 BSC	0.35	0.00	0.10	0.10	0.10	0.05	0.08
Nom	0.85	-		0.30			3.60	3.60		0.40						
Max	0.90	0.05		0.35			3.70	3.70		0.45	0.10					

The QFN24 package uses matte-Sn post plated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

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